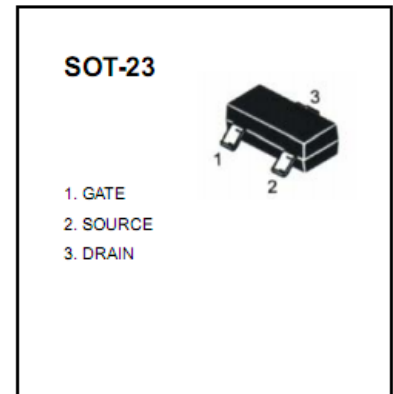
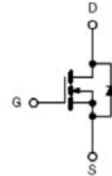


## SOT-23 Plastic-Encapsulate Transistors

### FEATURES

Trench FET Power MOSFET

MARKING: A2SHB



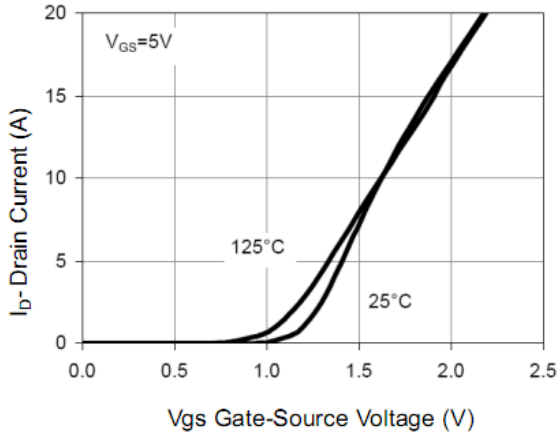
### MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-Source voltage	20	V
V <sub>GS</sub>	Gate-Source voltage	±10	V
I <sub>D</sub>	Drain current	2.9	A
P <sub>D</sub>	Power Dissipation	1	W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

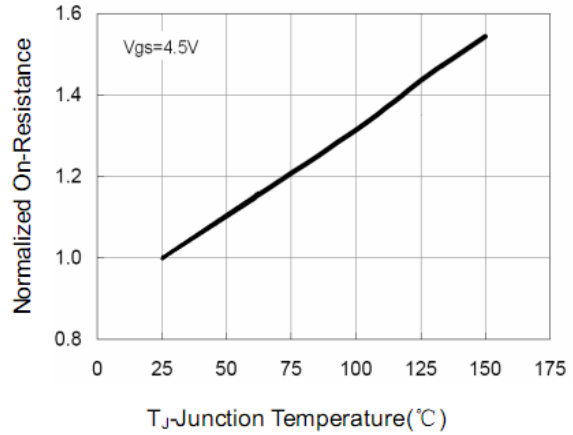
### ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Gate-Threshold Voltage	V <sub>th(GS)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA	0.5	0.75	1.2	V
Gate-body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μA
Drain-Source On-Resistance	r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A		37	59	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.9A		30	45	mΩ
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =2.9A		9.5		S
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		300		pF
Output Capacitance	C <sub>oss</sub>			120		
Reverse Transfer Capacitance	C <sub>rss</sub>			80		
Switching Capacitance						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =2.9A, V <sub>GS</sub> =4.5V R <sub>GEN</sub> =6Ω		10	15	nS
Turn-on Rise Time	t <sub>r</sub>			50	85	nS
Turn-off Delay Time	t <sub>d(off)</sub>			17	45	nS
Turn-off Fall Time	t <sub>f</sub>			10	20	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =2.9A, V <sub>GS</sub> =4.5V,		4.0	10	nC
Gate-Source Charge	Q <sub>gs</sub>			0.65		nC
Gate-Drain Charge	Q <sub>gd</sub>			1.2		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =2.9A		0.75	1.2	V
Diode Forward Current	I <sub>S</sub>				2.9	A

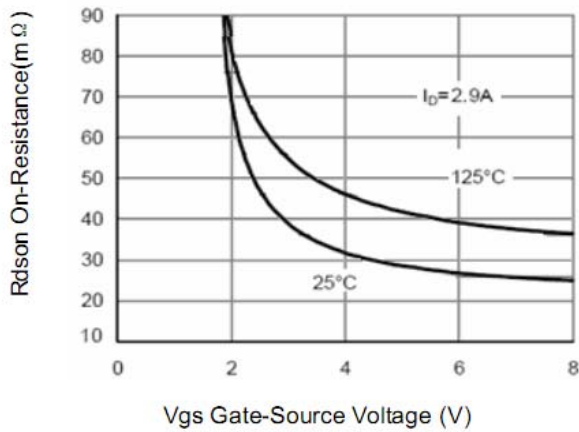
## Typical Characteristics



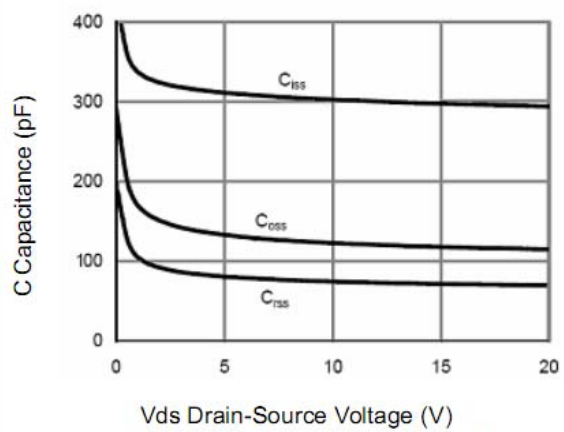
**Figure 7 Transfer Characteristics**



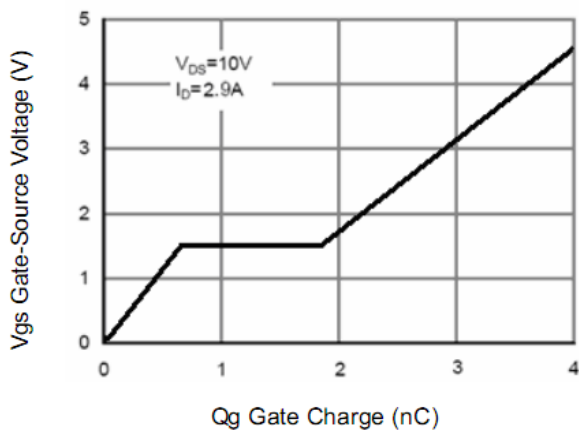
**Figure 8 Drain-Source On-Resistance**



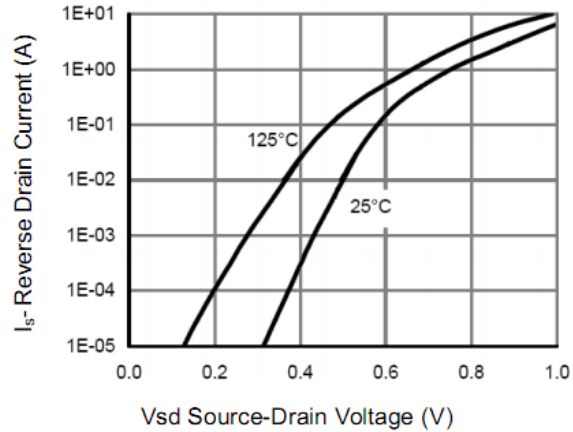
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**



**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**

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